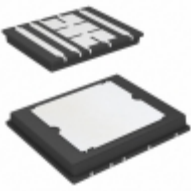

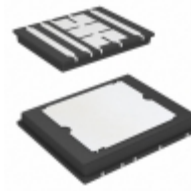


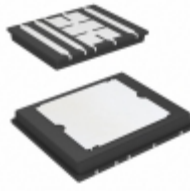
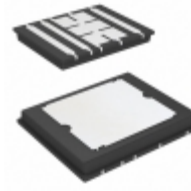
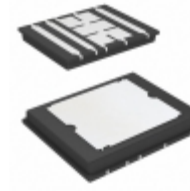
	<h2>SIE808DF-T1-E3</h2>
	<p>Hersteller-Teilenummer: SIE808DF-T1-E3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 20V 60A 10-POLARPAK</p> <p>Datenblätter:  SIE808DF-T1-E3.pdf</p> <p>RoHS Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 1690 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIE808DF-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 20V 60A 10-POLARPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	1690 pcs Stock
detaillierte Beschreibung	N-Channel 20V 60A (Tc) 5.2W (Ta), 125W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	10-PolarPAK® (L)
Supplier Device-Gehäuse	10-PolarPAK® (L)
Verlustleistung (max)	5.2W (Ta), 125W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	60A (Tc)
Rds On (Max) @ Id, Vgs	1.6 mOhm @ 25A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	155nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	8800pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIE808DF-T1-E3CT

SIE808DF-T1-E3 ist neu im Original, Suche SIE808DF-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIE808DF-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIE808DF-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIE810DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 60A POLARPAK</p>	 <p>SIE810DF-T1-E3 Vishay / Siliconix MOSFET N-CH 20V 60A 10- POLARPAK</p>	 <p>SIE806DF-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 60A POLARPAK</p>	 <p>SIE808DF-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 60A POLARPAK</p>
 <p>SIE806DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 60A POLARPAK</p>	 <p>SIE806DF-T1-E3 Vishay / Siliconix MOSFET N-CH 30V 60A 10- POLARPAK</p>	 <p>SIE808DF-T1-E3 Vishay / Siliconix MOSFET N-CH 20V 60A 10- POLARPAK</p>	 <p>SIE808DF-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 60A POLARPAK</p>

heiße Teile

Mehr

1206SFS800F/24	8800E12BBPF	AD1981BJSTZ	BYM10-1000	CL05X106MR5NUNC
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IPD80N04S3-06	ISL3178EIUZ	KSC5302DITU	LD6805K/18P	LEA-6T-1-001
MAZD220GMLS0	MBRD10200CT	MCD95-14io8	MSMBJ40AE3	NP40N10VDF
OP07AZ/883Q	PH600S280-48	RT9161-18PX	SI7726DN-T1-GE3	SIE01-03
SIE01-06	SIE20031	SIE20034	SIE501.8LT	SI5E03.3LT
SIE503.3LTR	SIE800DF-T1-E3	SIE800DF-T1-E3	SIE802DF-T1-E3	SIE802DF-T1-E3
SIE808DF-T1-E3	SIE812DF	SIE848DF-T1-E3	SIE848DF-T1-E3	SIE862DF-T1-GE3
SIE862DF-T1-GE3	SIE864DP-T1-GE3	SIE874DF-T1-GE3	SIE874DF-T1-GE3	SIR474DP-T1-E3
STB30NS15T4	T102F02VBC	TPS79733DCKT	UC2844D8TRG4	VS-15MQ040NPBF

Contact us:Info@Y-IC.com

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